

#### **Product Summary**

Device	V <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C	
Q1	30V	1.5Ω @ V <sub>GS</sub> = 4.5V	250mA	
QI	300	$2.0\Omega @ V_{GS} = 2.5V$	350mA	

#### Description

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$ , yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# Applications

- Motor Control
- Power Management Functions

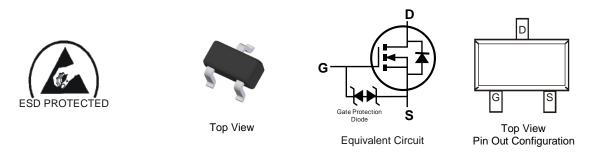
#### Features

- Low On-Resistance: R<sub>DS(ON)</sub>
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin Annealed over Alloy 42
  Leadframe. Solderable per MIL-STD-202, Method 208 (9)
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)

#### SOT523



### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN31D6UT-7	SOT523	3,000/Tape & Reel
DMN31D6UT-13	SOT523	10,000/Tape & Reel

Notes: 1. No p

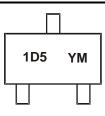
No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



# **Marking Information**



1D5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Year	2014	2	2015	2016		2017	2018		2019		2020		2021
Code	В		С	D		E	F		G		Н		Ι
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Au	ig S	ер	Oct	Νον	/ Dec
Code	1	2	3	4	5	6	7	8		9	0	N	D

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	30	V
Gate-Source Voltage		V <sub>GSS</sub>	±12	V
Drain Current (Note 6)	Continuous	I <sub>D</sub>	350	mA
Pulsed Drain Current (Note 6)		I <sub>DM</sub>	800	mA

# **Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		PD	210	mW
Thermal Desistance, lunction to Ambient (Note 5)	Steady State	D	593	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	R <sub>θJA</sub>	542	C/VV
Total Power Dissipation (Note 6)		PD	320	mW
Thermal Basistones, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	398	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<5s		363	C/VV
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

Notes:

Device mounted on FR-4 PCB, with minimum recommended pad layout
 Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.



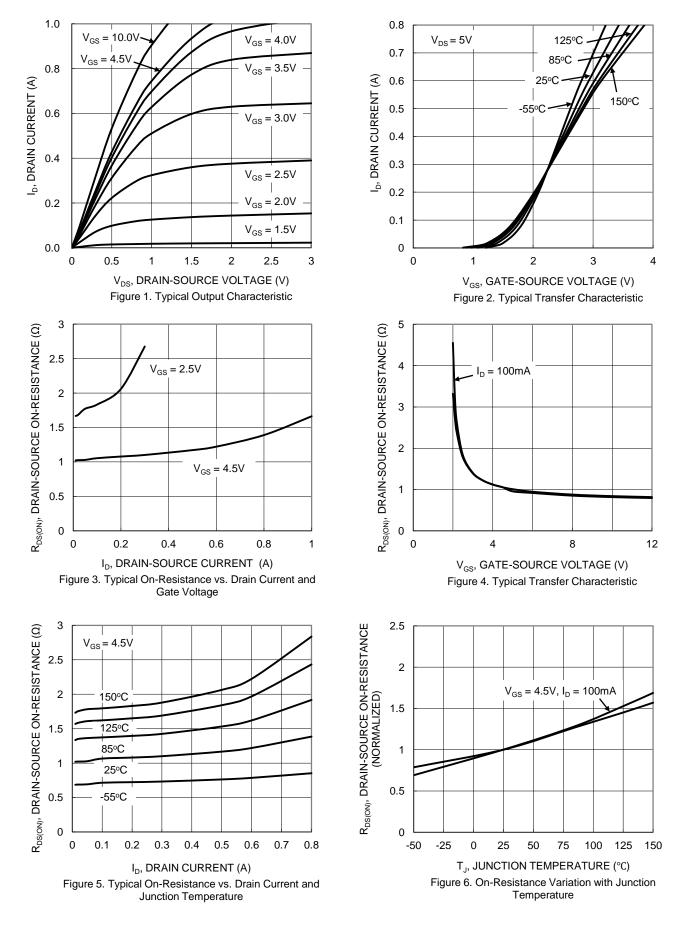
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	—	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current @T <sub>C</sub> = +25°C			_	100	nA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.4		1.4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Б	_	1.1	1.5	Ω	$V_{GS} = 4.5V, I_D = 100mA$	
	R <sub>DS(ON)</sub>		1.6	2.0	12	$V_{GS} = 2.5V, I_D = 50mA$	
Diode Forward Voltage	V <sub>SD</sub>		0.6	1.0	V	$V_{GS} = 0V, I_S = 10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance Output Capacitance		_	13.6	—	pF		
		_	3.1	—	pF	$V_{DS} = 15V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		2.2	—	pF		
Total Gate Charge	Qg		0.35	—	nC		
Gate-Source Charge	Q <sub>gs</sub>	_	0.06	—	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$	
Gate-Drain Charge	Q <sub>gd</sub>	_	0.19	—	nC	$-I_{D} = 200 \text{mA}$	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.3	_	ns		
Turn-On Rise Time Turn-Off Delay Time		_	2.3	_	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 4.5V,	
		_	7.4	—	ns	$R_{G} = 2\Omega, I_{D} = 200 \text{mA}$	
Turn-Off Fall Time	t <sub>D(OFF)</sub>	_	4.4	_	ns	1	

Notes: 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.

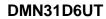


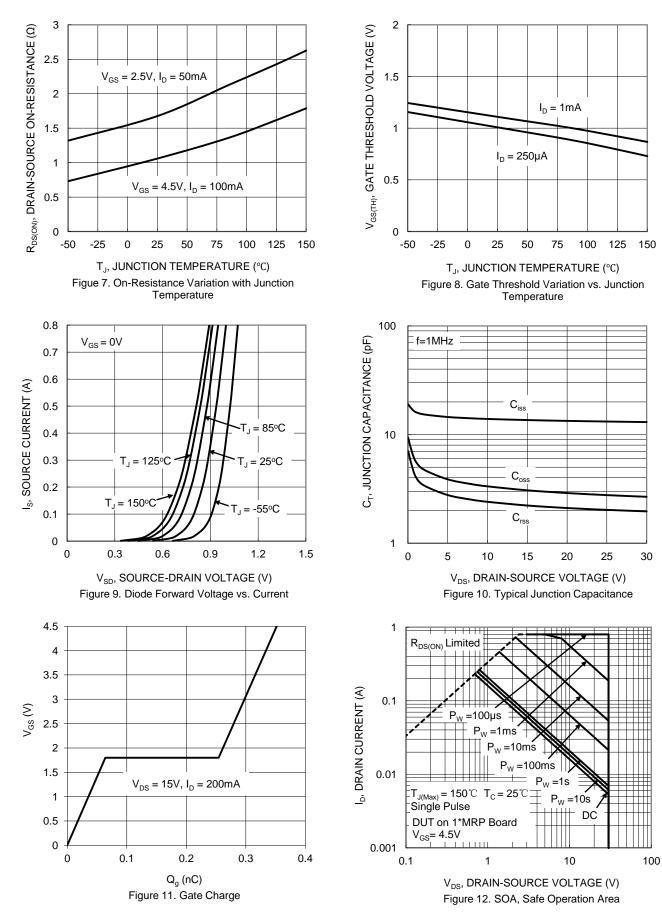
### DMN31D6UT



DMN31D6UT Document number: DS38191 Rev. 1 - 2

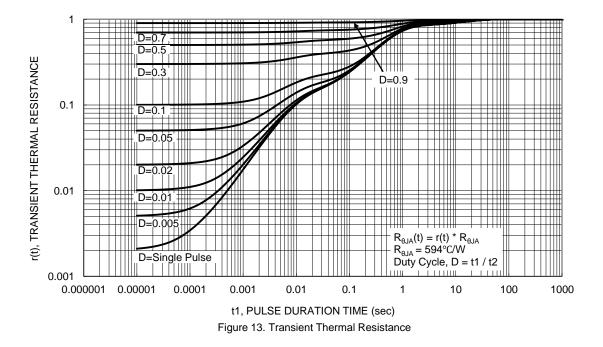






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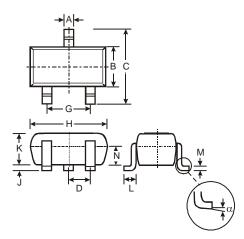


# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

SOT523

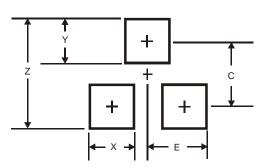
SOT523



SOT523							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.22				
В	0.75	0.85	0.80				
С	1.45	1.75	1.60				
D	_	_	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
J	0.00	0.10	0.05				
κ	0.60	0.80	0.75				
L	0.10	0.30	0.22				
Μ	0.10	0.20	0.12				
Ν	0.45	0.65	0.50				
α	0°	8°					
All	All Dimensions in mm						

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	1.8
Х	0.4
Y	0.51
C	1.3
E	0.7



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